



30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-100 A

Features

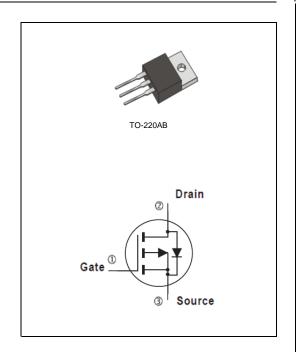
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-20A<5m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-15A<7.5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.. (Halogen Free)



• Case: TO-220AB Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0667 ounces, 1.89 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V_{GS}	<u>+</u> 20	٧
Continuous Drain Current	T _C =25°C	l _D	-100	
	T _C =100°C		-63	Α
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-400	
Power Dissipation	T _C =25°C	Po	119	14/
	T _C =100°C		48	W
Continuous Drain Current	T _A =25°C	I _D	-15.8	А
	T _A =70°C		-12.6	А
Power Dissipation	T _A =25°C	-	2.0	14/
Power Dissipation	T _A =70°C	Pb	1.3	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	1.05	90.444
	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1	-1.6	-2.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-20A	-	3.9	5	mΩ		
		V _{GS} =-4.5V,I _D =-15A	-	5.7	7.5			
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-30V, V_{GS} =0V	-	-	-1	uA		
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 6)								
Total Gate Charge	Q_{g}	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V ^(Note 2,3)	-	107	-	nC		
Gate-Source Charge	Q_gs		-	18	-			
Gate-Drain Charge	Q_{gd}	V _{GS} =-10V	-	18	-			
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V,	-	6067	-	pF		
Output Capacitance	Coss		-	709	-			
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	361	-			
Turn-On Delay Time	td _(on)	\/ 45\/ 1 40	-	22	-	ns		
Turn-On Rise Time	t _r	V_{DS} =-15V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 2,3)	-	48	-			
Turn-Off Delay Time	td _(off)		-	197	-			
Turn-Off Fall Time	t _f		-	90	-			
Drain-Source Diode								
Maximum Continuous Drain-Source					100	Α		
Diode Forward Current	I _S		-	-	-100	A		
Diode Forward Voltage	V _{SD}	I _S =-1A,V _{GS} =0V	-	-0.68	-1	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

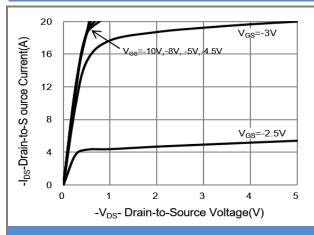


Fig.1 Output Characteristics

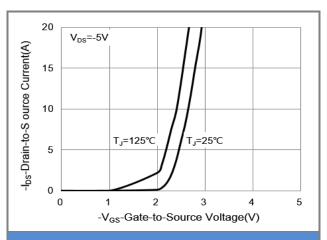


Fig.2 Transfer Characteristics

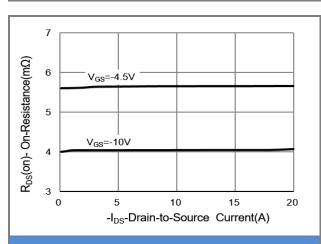


Fig.3 On-Resistance vs. Drain Current

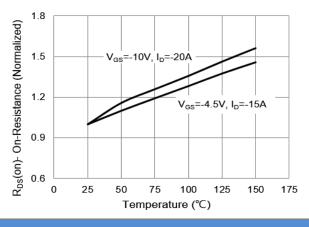
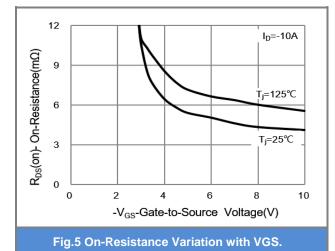


Fig.4 On-Resistance vs. Junction Temperature



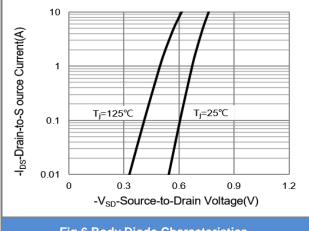


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

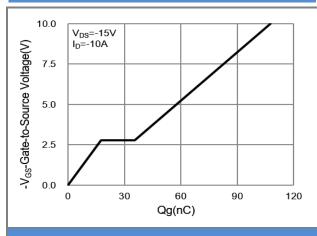


Fig.7 Gate Charge

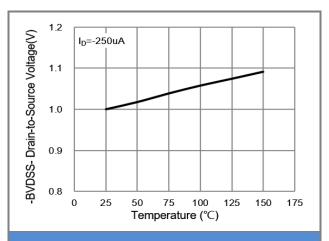


Fig.8 Breakdown Voltage Variation vs. Temperature

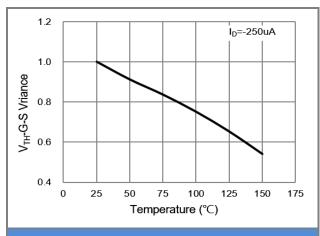


Fig.9 Threshold Voltage Variation with Temperature

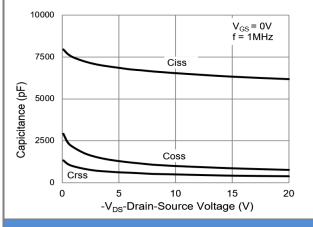


Fig.10 Capacitance vs. Drain-Source Voltage

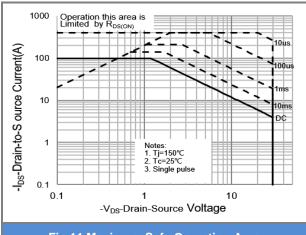


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

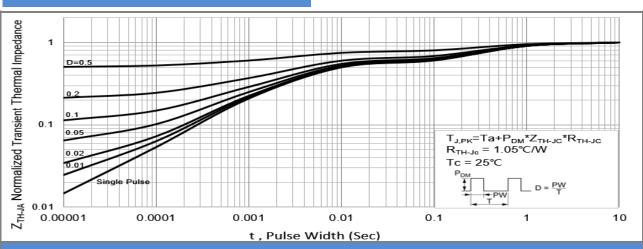
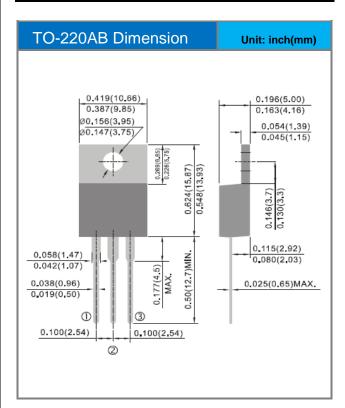


Fig.12 PJP100P03 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information







PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJP100P03_T0_00001	TO-220AB	50pcs / Tube	P100P03	Halogen free





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